

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Withdrawn) A circuit comprising:

a MOS transistor having a cap layer comprised of a high dielectric constant material.

2. (Withdrawn) The circuit of Claim 1 wherein said high dielectric constant material is hafnium silicon oxynitride.

3. (Withdrawn) The circuit of Claim 1 wherein said MOS transistor is a PMOS transistor.

4. (Currently Amended) A circuit comprising:

a NMOS transistor, said NMOS transistor having a gate oxide, a lightly doped drain coupled to said gate oxide, and a cap layer coupled to a majority of a top surface of said lightly doped drain but separated from said gate oxide by a layer of oxide coupled to said lightly doped drain and a layer of nitride coupled to said lightly doped drain, said cap layer comprised of a high dielectric constant material.

5. (Withdrawn) A MOS transistor comprising:

a cap layer comprised of a high dielectric constant material.

6. (Withdrawn) The MOS transistor of Claim 5 wherein said high dielectric constant material is hafnium silicon oxynitride.

7. (Currently Amended) A NMOS transistor comprising:

a gate oxide;

a lightly doped drain coupled to said gate oxide; and

a cap layer coupled to a majority of a top surface of said lightly doped drain but separated from said gate oxide by a layer of oxide coupled to said lightly doped drain and a layer of nitride coupled to said lightly doped drain, said cap layer comprised of a high dielectric constant material.

8. (Withdrawn) The MOS transistor of Claim 5 wherein said MOS transistor is a PMOS transistor.

9. (Withdrawn) A PMOS transistor comprising:

a cap layer comprised of a high dielectric constant material.

10. (Withdrawn) The PMOS transistor of Claim 9 wherein said high dielectric constant material is hafnium silicon oxynitride.

11. (Withdrawn) A PMOS transistor comprising:
a cap layer comprised of hafnium silicon oxynitride.

12. (New) The circuit of Claim 4 wherein said high dielectric constant material is hafnium silicon oxynitride.

13. (New) The NMOS transistor of Claim 7 wherein said high dielectric constant material is hafnium silicon oxynitride.